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|  | <p>SI7772DP-T1-GE3</p> |
| | <p>Hersteller-Teilenummer: SI7772DP-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 35.6A PPAK SO-8</p> <p>Datenblätter:  SI7772DP-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 20645 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |
| <p>Image may be representation. See specs for product details.</p> | |

Spezifikationen

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| Teilenummer | SI7772DP-T1-GE3 |
| Hersteller | Vishay / Siliconix |
| Beschreibung | MOSFET N-CH 30V 35.6A PPAK SO-8 |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs , |
| Teilstatus | 20645 pcs Stock |
| Serie | SkyFET®, TrenchFET® |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | PowerPAK® SO-8 |
| Supplier Device-Gehäuse | PowerPAK® SO-8 |
| Verlustleistung (max) | 3.9W (Ta), 29.8W (Tc) |
| Typ FET | N-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 30V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 35.6A (Tc) |
| Rds On (Max) @ Id, Vgs | 13 mOhm @ 15A, 10V |
| VGS (th) (Max) @ Id | 2.5V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 28nC @ 10V |
| Eingabekapazität (Ciss) (Max) @ Vds | 1084pF @ 15V |
| Verpackung | Tape & Reel (TR) |

SI7772DP-T1-GE3 ist neu im Original, Suche SI7772DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7772DP-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI7772DP-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

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|  <p>SI7772DP-T1-E3 VISHAY VISHAY PAKSO-8</p> |  <p>SI7758DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 60A PPAK SO-8</p> |  <p>SI7784DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 35A PPAK SO-8</p> |  <p>SI7758DP VB SI7758DP VB</p> |
|  <p>SI7784DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 35A PPAK SO-8</p> |  <p>SI7774DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 60A PPAK SO-8</p> |  <p>SI7774DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 60A PPAK SO-8</p> |  <p>SI7748DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 50A PPAK SO-8</p> |

heiße Teile

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|  SI7716ADN-T1-GE3 |  SI7716DN-T1-GE3 |  SI7720DN-T1-E3 |  SI7720DN-T1-GE3 |  SI7720DN-T1-GE3 |
|  SI7726DN |  SI7726DN-T1-E3 |  SI7726DN-T1-GE3 |  SI7726DN-T1-GE3 |  SI7732DP-T1-GE3 |
|  SI7738DP |  SI7738DP-T1-3 |  SI7738DP-T1-E3 |  SI7738DP-T1-E3 |  SI7738DP-T1-GE3 |
|  SI7738DP-T1-GE3 |  SI7742DP-T1-E3 |  SI7742DP-T1-GE3 |  SI7742DP-T1-GE3 |  SI7748DP-T1-GE3 |
|  SI7748DP-T1-GE3 |  SI7758DP |  SI7758DP-T1-GE3 |  SI7758DP-T1-GE3 |  SI7772DP-T1-GE3 |
|  SI7774DP-T1-GE3 |  SI7774DP-T1-GE3 |  SI7784DP-T1-GE3 |  SI7784DP-T1-GE3 |  SI7788DP-T1-GE3 |
|  SI7788DP-T1-GE3 |  SI7790DP-T1-E3 |  SI7790DP-T1-GE3 |  SI7790DP-T1-GE3 |  SI7792DP-T1-GE3 |
|  SI7792DP-T1-GE3 |  SI7794DP-T1-GE3 |  SI7794DP-T1-GE3 |  SI7798DP-T1-GE3 |  SI7804DN |
|  SI7804DN-T1-E3 |  SI7804DN-T1-E3 |  SI7806ADN |  SI7806ADN-T1-E3 |  SI7806ADN-T1-E3 |
|  SI7806ADN-T1-E3-PBF |  SI7806ADN-T1-GE3 |  SI7806ADN-T1-GE3 |  SI7806AEDN-T1-E3 |  SI7806BDN |

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